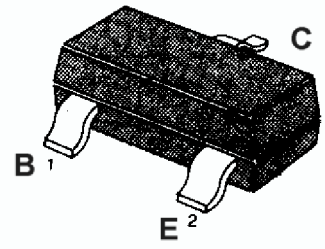


**APPLICATION:** High-Frequency Amplifier Applications.

**MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CBO</sub>	20	V
Collector-emitter voltage	V <sub>CEO</sub>	11	V
Emitter-base voltage	V <sub>EBO</sub>	3	V
Collector current	I <sub>C</sub>	50	mA
Collector Power Dissipation	P <sub>C</sub>	150	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C

**SOT-23**


1.Base 2.Emitter 3.Collector

**ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	27		270		V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA
Collector Cut-off Current	I <sub>CBO</sub>			0.5	μA	V <sub>CB</sub> = 10V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			0.5	μA	V <sub>EB</sub> = 2V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	20			V	I <sub>C</sub> = 0.01mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	11			V	I <sub>C</sub> = 1mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	3			V	I <sub>E</sub> = 0.01mA, I <sub>C</sub> =0
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			0.5	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 5mA
Gain bandwidth product	f <sub>T</sub>	1.4	3.2		GHz	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V, f = 500MHz
Common Base Output Capacitance	C <sub>ob</sub>		0.8	1.5	PF	V <sub>CB</sub> = 10V, I <sub>E</sub> =0, f = 1MHz
Noise Figure	N <sub>F</sub>		3.5		dB	V <sub>CE</sub> = 6V, I <sub>C</sub> = 2mA, f= 500MHz, R <sub>g</sub> = 50Ω

**h<sub>FE</sub> Classification And Marking**

Print Mark AD

Classification

 h<sub>FE</sub> 27~270